-100V, 55mΩ typ., -30A P-Channel MOSFET

General Description

The 30P10 uses advanced process technology and design to provide excellent $R_{DS(ON)}$. It can be used in a wide variety of applications.

Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
-100V	63mΩ	-30A

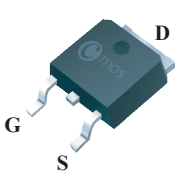
Applications

- Motor Drivers
- Switching Voltage Regulators

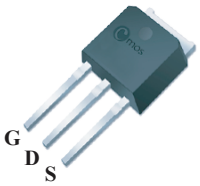
Features

- P-Channel MOSFET
- Low ON-resistance
- 100% avalanche tested
- RoHS Compliant

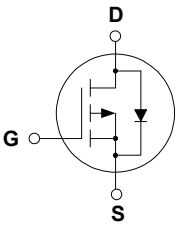
TO-252/251 Pin Configuration



TO-252
(CMD30P10)



TO-251
(CMU30P10)



Absolute Maximum Ratings (T_A=25 ℃ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current	-30	A
I_D@T_C=100℃	Continuous Drain Current	-21	A
I_{DM}	Pulsed Drain Current	-120	A
EAS	Single Pulse Avalanche Energy[1]	312	mJ
P_D@T_C=25℃	Total Power Dissipation	120	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	1.04	℃/W

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Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250μA	-100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V , I_D=-15A	---	55	63	mΩ
		V_{GS}=-4.5V , I_D=-10A	---	57	70	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D = -250μA	-1.0	---	-3.0	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-100V , V_{GS}=0V	---	---	-1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS} = ±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS} =-10V , I_D=-15A	---	25	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	12	---	Ω
Q_g	Total Gate Charge	V_{DS}=-80V , V_{GS}=-10V , I_D=-15A	---	70	---	nC
Q_{gs}	Gate-Source Charge		---	10	---	
Q_{gd}	Gate-Drain Charge		---	20	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=-50V, V_{GS} =-10V , R_G =4.7Ω I_D=-10A	---	30	---	ns
T_r	Rise Time		---	12	---	
$T_{d(off)}$	Turn-Off Delay Time		---	290	---	
T_f	Fall Time		---	41	---	
C_{iss}	Input Capacitance	V_{DS}=-25V , V_{GS}=0V , f=1MHz	---	6700	---	pF
C_{oss}	Output Capacitance		---	170	---	
C_{rss}	Reverse Transfer Capacitance		---	130	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	-30	A
I_{SM}	Pulsed Source Current		---	---	-120	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=-20A ,T_J=25℃	---	-0.86	-1.2	V

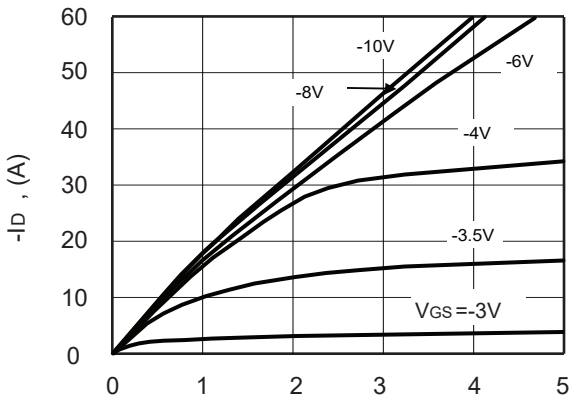
Note :

1.The EAS data shows Max. rating . The test condition is V_{DD}=-50V , V_{GS}=-10V , L=1mH , I_{AS}=-25A.

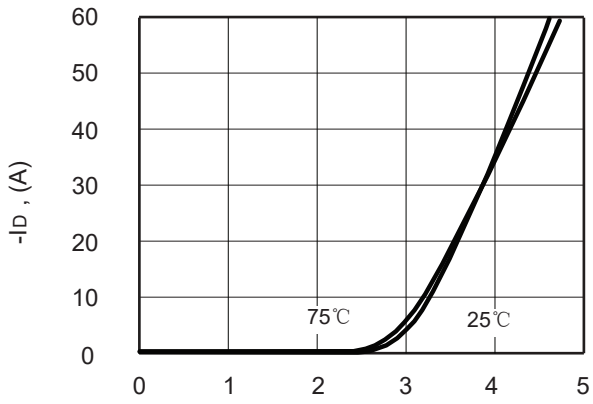
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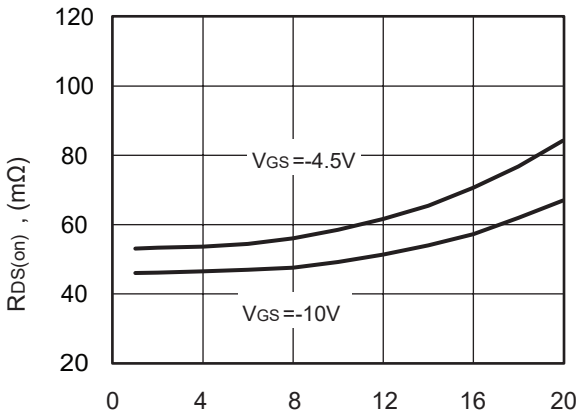
Typical Characteristics



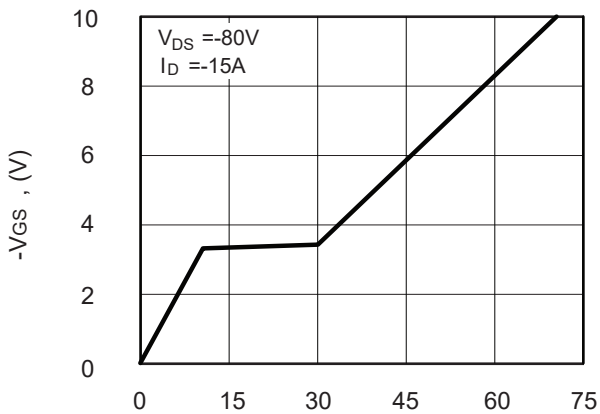
Output Characteristics



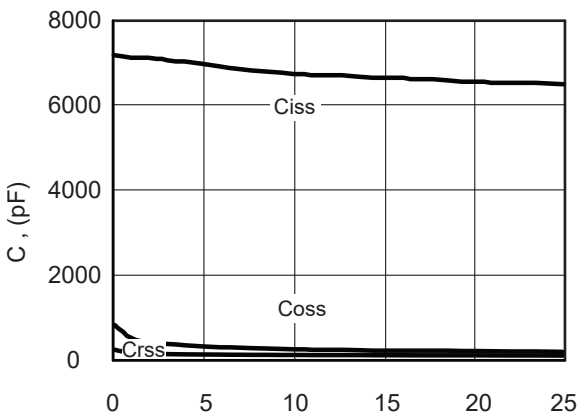
transfer characteristics



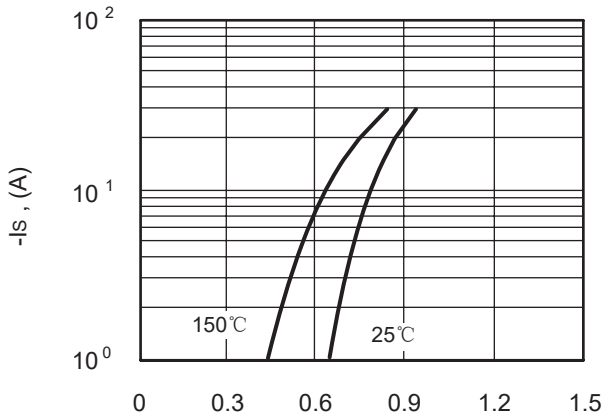
On-Resistance vs. Drain Current



Gate Charge Characteristics



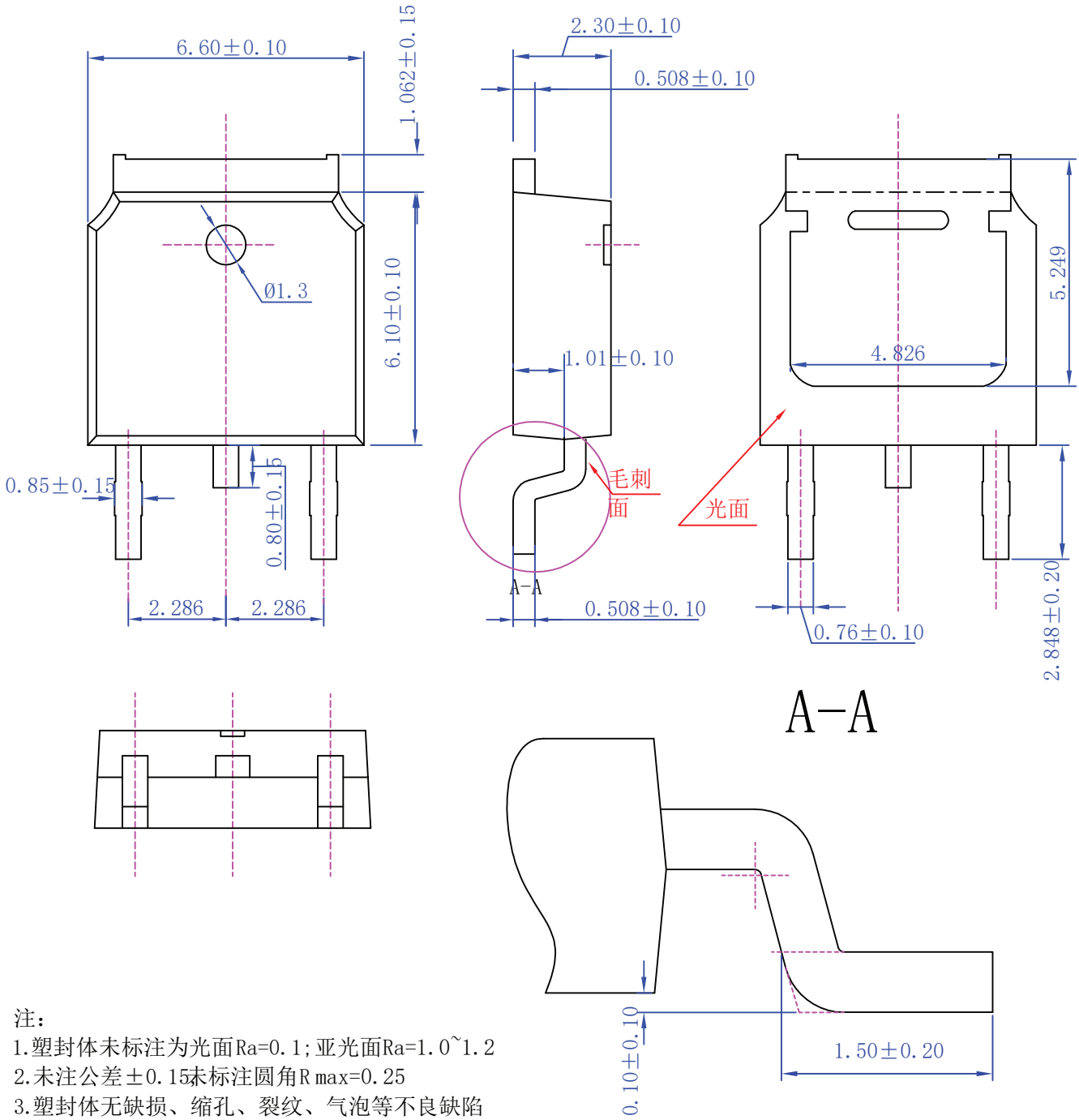
Capacitance Characteristics



Body-Diode Characteristics

Package Dimension

TO-252 Unit :mm



注：
1.塑封体未标注为光面Ra=0.1;亚光面Ra=1.0~1.2
2.未注公差±0.15未标注圆角R max=0.25
3.塑封体无缺损、缩孔、裂纹、气泡等不良缺陷
4.标注单位mm
5.顶针孔不允许凸出塑封体表面

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Package Dimension

TO-251A Unit :mm

